

Transistor		Transistor	
Elektrische Eigenschaften		Electrical properties	
Höchstzulässige Werte		Maximum rated values	
V_{CES}		1200	V
I_C		400	A
I_{CRM}	$t_p = 1 \text{ ms}$	800	A
P_{tot}	$t_C = 25^\circ\text{C}$	2400	W
V_{GE}		20	V
V_{EG}		20	V

Charakteristische Werte		Characteristic values	
$V_{CE \text{ sat}}$	$i_{CM} = 400 \text{ A}, V_{GE} = 15 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ.	3 V
	$i_{CM} = 400 \text{ A}, V_{GE} = 15 \text{ V}, t_{vj} = 25^\circ\text{C}$	max.	4 V
$V_{GE} \text{ (th)}$	$V_{CE} = 5 \text{ V}, i_C = 400 \text{ mA}, t_{vj} = 25^\circ\text{C}$	min.	3 V
	$V_{CE} = 5 \text{ V}, i_C = 400 \text{ mA}, t_{vj} = 25^\circ\text{C}$	max.	6 V
C_{ies}	$V_{CE} = 10 \text{ V}, V_{GE} = 0 \text{ V}, f_o = 1 \text{ MHz}, t_{vj} = 25^\circ\text{C}$	typ.	60 nF
	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ.	1 mA
i_{CES}	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}, t_{vj} = 125^\circ\text{C}$	typ.	8 mA
	$V_{GE} = 20 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ.	50 nA
i_{GES}	$V_{GE} = 20 \text{ V}, t_{vj} = 25^\circ\text{C}$	max.	500 nA
	$V_{EG} = 20 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ.	50 nA
i_{EGS}	$V_{EG} = 20 \text{ V}, t_{vj} = 25^\circ\text{C}$	max.	500 nA
	$i_{CM} = 400 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 25^\circ\text{C}$	typ.	0,4 μs
t_{on}	$i_{CM} = 400 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 125^\circ\text{C}$	typ.	0,6 μs
	$i_{CM} = 400 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, V_{LR} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 25^\circ\text{C}$	typ.	0,6 μs
t_s	$i_{CM} = 400 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, V_{LR} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 125^\circ\text{C}$	typ.	0,9 μs
	$i_{CM} = 400 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, V_{LR} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 25^\circ\text{C}$	typ.	0,2 μs
t_f	$i_{CM} = 400 \text{ A}, V_{CE} = 600 \text{ V}, V_{LF} = 15 \text{ V}, V_{LR} = 15 \text{ V}, R_G = 2,4 \Omega, t_{vj} = 125^\circ\text{C}$	typ.	0,3 μs

Bedingungen für den Kurzschlußschutz	Conditions for protection against short circuits
$t_{ig} = 10 \mu\text{s}$	$V_{CC} = 750 \text{ V}$
$V_{LF} = V_{LR} = 15 \text{ V}$	$V_{CEM} = 1000 \text{ V}$
$R_G = 2,4 \Omega$	$i_{CMK 1} \approx 4500 \text{ A}$
$t_{vj} = 125^\circ\text{C}$	$i_{CMK 2} \approx 3200 \text{ A}$

Thermische Eigenschaften		Thermal properties	
R_{thJC}	DC, pro Baustein / per module	0,052	$^\circ\text{C/W}$
R_{thCK}	pro Baustein / per module	0,03	$^\circ\text{C/W}$
$t_{vj \text{ max}}$		150	$^\circ\text{C}$
$t_{vj \text{ op}}$		- 40 / + 150	$^\circ\text{C}$
t_{stg}		- 40 / + 125	$^\circ\text{C}$

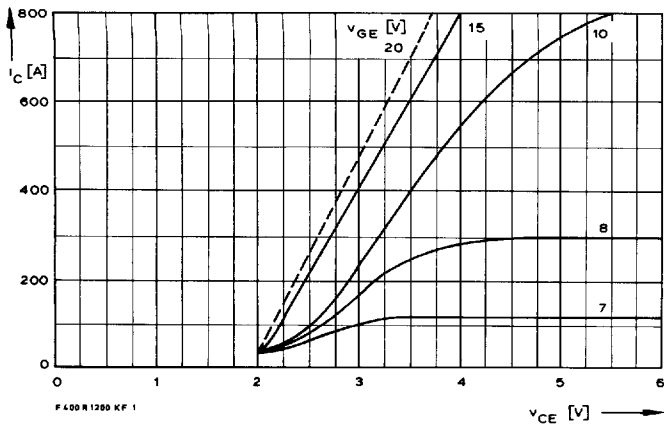
Inversdiode		Inverse diode	
Elektrische Eigenschaften		Electrical properties	
Höchstzulässige Werte		Maximum rated values	
$I_{F \text{ (max)}}$		400	A
I_{FRM}	$t_p = 1 \text{ ms}$	800	A

Charakteristische Werte		Characteristic values	
V_F	$i_F = 400 \text{ A}, V_{GE} = 0 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ.	2 V
	$i_F = 400 \text{ A}, V_{GE} = 0 \text{ V}, t_{vj} = 25^\circ\text{C}$	max.	3 V
I_{RM}	$i_{FM} = 400 \text{ A}, -di_F/dt = 300 \text{ A}/\mu\text{s}, V_{EG} = 10 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ.	28 A
	$i_{FM} = 400 \text{ A}, -di_F/dt = 300 \text{ A}/\mu\text{s}, V_{EG} = 10 \text{ V}, t_{vj} = 125^\circ\text{C}$	typ.	52 A
Q_r	$i_{FM} = 400 \text{ A}, -di_F/dt = 300 \text{ A}/\mu\text{s}, V_{EG} = 10 \text{ V}, t_{vj} = 25^\circ\text{C}$	typ.	4 μAs
	$i_{FM} = 400 \text{ A}, -di_F/dt = 300 \text{ A}/\mu\text{s}, V_{EG} = 10 \text{ V}, t_{vj} = 125^\circ\text{C}$	typ.	17 μAs

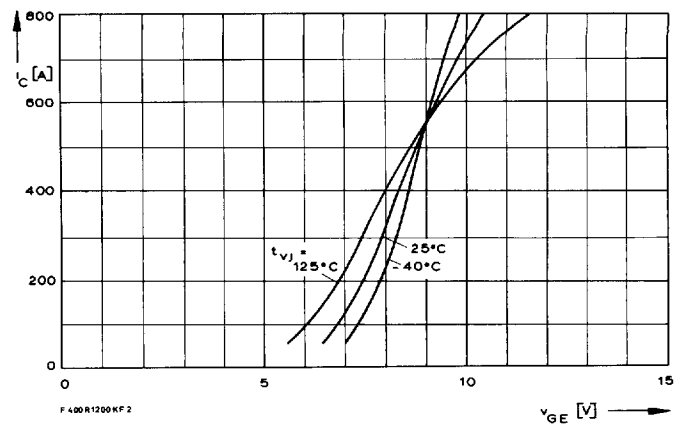
Thermische Eigenschaften		Thermal properties	
R_{thJC}	DC, pro Baustein / per module	0,2	$^\circ\text{C/W}$
R_{thCK}	DC, pro Zweig / per arm pro Baustein / per module pro Zweig / per arm	0,03	$^\circ\text{C/W}$
$t_{vj \text{ max}}$		125	$^\circ\text{C}$
$t_{vj \text{ op}}$		- 40 / + 125	$^\circ\text{C}$
t_{stg}		- 40 / + 125	$^\circ\text{C}$

Innere Isolation	Internal insulation
Isoliermaterial: Al N	Insulating material: Al N
V_{ISOL} RMS (f=50 Hz, t=1 min)	2,5 kV

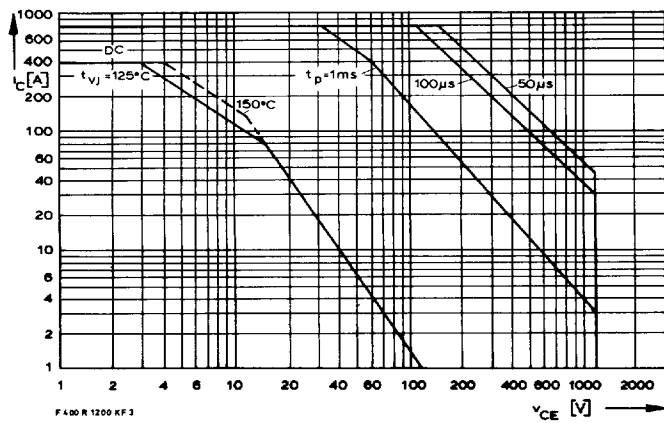
Mechanische Eigenschaften		Mechanical properties	
G		465	g
M 1		3	Nm
M 2	terminals M 4 / M 6	2 Nm / 3	Nm
Maßbild	Seite 183, Nr. 5	outline	page 183, no. 5



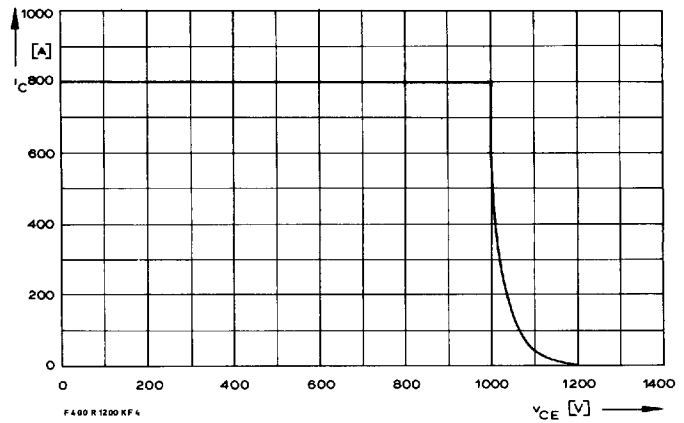
1 Kollektor-Emitter-Spannung im Sättigungsbereich (typisch).
Collector-emitter-voltage in saturation region (typical).
 $t_{vj} = 25^\circ\text{C}$



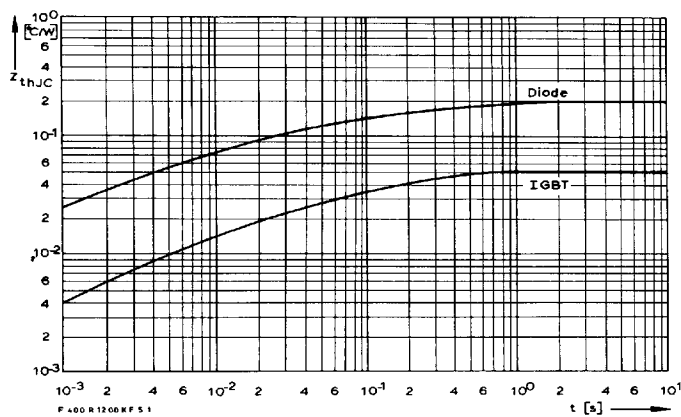
2 Übertragungscharakteristik (typisch).
Transfer characteristic (typical).
 $V_{CE} = 5\text{ V}$



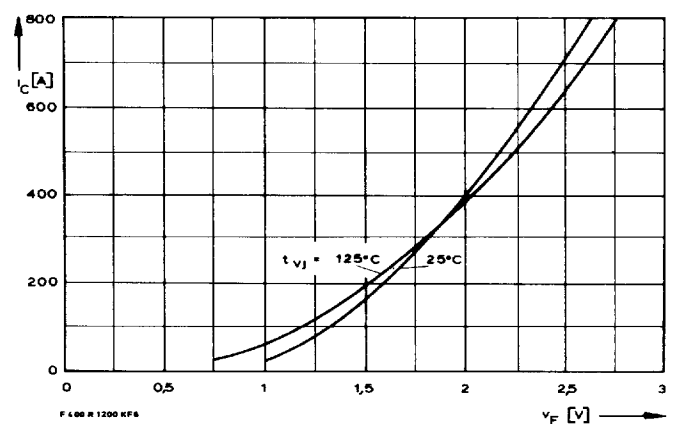
3 Vorwärts-Arbeitsbereich FBSOA (Einzelimpuls, nicht periodisch).
Forward biased safe operating area (single pulse, non repetitive).
 $t_C = 25^\circ\text{C}$



4 Rückwärts-Arbeitsbereich RBSOA.
Reverse biased safe operating area.
 $t_{vj} = 125^\circ\text{C}$, $V_{LF} = V_{LR} = 15\text{ V}$, $R_G = 2,4\ \Omega$



5 Transienter innerer Wärmewiderstand je Zweig (DC).
Transient thermal impedance per arm (DC)



6 Durchlaßkennlinie der Inversdiode (typisch).
Forward characteristic of the inverse diode (typical)
 $V_{GE} = 0\text{ V}$

3403297 0002011 19T